



PTO/SB/08B (07-05)
Approved for use through 07/31/2006. OMB 0651-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Complete if Known

Application Number	10/799318
Filing Date	Mar 12, 2004
First Named Inventor	Randy Hoffman
Art Unit	
Examiner Name	Unassigned
Attorney Docket Number	200315719-1

Sheet 2 of 2

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MLP		Proceedings of the IEEE, Proceedings Letters, November 1968, pgs 2094-2095.	
MLP		Extended abstracts of the 2000 International Conference on Solid State Devices and Materials; Aug 29-31, 2000, Sendai Intl Center, pgs 128-129.	
MLP		OHTOMO, "Novel Semiconductor Technologies of ZnO Films towards...", IEICE Trans. Electron., Vol E83-C, No 10, Oct 2000, pgs 1614-1617.	

Examiner Signature		Date Considered	3/19/2007
-----------------------	--	--------------------	-----------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.

#2 IDS
3/12/4

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

200315719-1

APPLICATION NO.

CONFIRMATION NO.

APPLICANT

Randy L. Hoffman, et al.

FILING DATE

Herewith

GROUP

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
MP	1A	4,887,255	12/12/1989	Handa, et al.	
	1B	5,744,864	04/28/1998	Cillelsen, et al.	
	1C	6,225,655	05/01/2001	Moise, et al.	
	1D	6,255,130	07/03/2001	Kim	
	1E	6,362,499	03/26/2002	Moise, et al.	
	1F	6,563,174	05/13/2003	Kawasaki, et al.	
	1G	2003/0013261	01/16/2003	Asano	
	1H	2002/0153587	10/24/2002	Adkisson, et al.	
	1I	2003/0207502	11/06/2003	Yamazaki, et al.	
	1J	2003/0218221	11/27/2003	Wager, III, et al.	
MP	1K	2003/0218222	11/27/2003	Wager, III, et al.	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
MP	1L	WO 97/06544	02/20/1997	Cillelsen, et al.		
MP	1M	EP1134811	09/19/2001	Kawasaki, et al.		
	1N					
	1O					
	1P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

MP	1Q	Aoki, Akira, et al., "Tin Oxide Thin Film Transistors", Japan J. Appl. Phys., Vol. 9, p.582 (1970).
MP	1R	Carcia, P.F., et al., "Transparent ZnO thin-film transistor fabricated by rf magnetron sputtering", Applied Physics Letters, Vol. 82, No. 7, pp. 1117-1119 (February 17, 2003).
MP	1S	Carcia, P.F., et al., "ZnO Thin Film Transistors for Flexible Electronics", Mat. Res. Soc. Symp. Proc., Vol. 769, pp. H72.1-H72.6 (2003).

EXAMINER

DATE CONSIDERED

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

200315719-1

APPLICATION NO.

CONFIRMATION NO.

APPLICANT

Randy L. Hoffman, et al.

FILING DATE

Herewith

GROUP

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
MP	2A	2003/0219530	11/27/2003	Yamazaki, et al.	
	2B	2003/0111663	06/19/2003	Yagi	
	2C	2003/0047785	03/13/2003	Kawasaki, et al.	
	2D	60/490,239	07/25/2003		Transparent Thin Film Transistor with Zinc-Tin Oxide Channel...
	2E	10/763,353	01/23/2004		Semiconductor Device
MP	2F	10/763,354	01/23/2004		Transistor including a Deposited Channel Region Having a ...
	2G				
	2H				
	2I				
	2J				
	2K				

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	2L					
	2M					
	2N					
	2O					
	2P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

MP	2Q	Fu, Shelton, et al., "MOS and MOSFET with Transistion Metal Oxides", SPIE Vol. 2697, pp. 520-527.
MP	2R	Giesbers, J.B., et al., "Dry Etching of All-Oxide Transparent Thin Film Memory Transistors", Microeletronic Engineering, Vol. 35, pp. 71-74 (1997).
MP	2S	Grosse-Holz, K.O., et al. "Semiconductive Behavior of Sb Doped SnO2 Thin Films", Mat. Res. Soc. Symp. Proc., Vol. 401, pp. 67-72 (1996).

EXAMINER

DATE CONSIDERED

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

200315719-1

APPLICATION NO.

CONFIRMATION NO.

APPLICANT

Randy L. Hoffman, et al.

FILING DATE

Herewith

GROUP

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	3A				
	3B				
	3C				
	3D				
	3E				
	3F				
	3G				
	3H				
	3I				
	3J				
	3K				

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	3L					
	3M					
	3N					
	3O					
	3P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

MP	3Q	Hoffman, R.L., et al., "ZnO-based transparent thin-film transistors", Applied Physics Letters, Vol. 82, No. 5, pp. 733-735 (February 3, 2003).
MP	3R	Masuda, Satoshi, et al., "Transparent thin film transistors using ZnO as an active channel layer and their electrical properties", Journal of Applied Physics, Vol. 93, No. 3, pp. 1624-1630 (February 1, 2003).
MP	3S	Nishi, Junya, et al., "High Mobility Thin Film Transistors with Transparent ZnO Channels", Jpn. J. Appl. Phys., Vol. 42, Part 2, No. 4A, pp. L347-L349 (April, 2003).

EXAMINER

DATE CONSIDERED

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

200315719-1

APPLICATION NO.

CONFIRMATION NO.

APPLICANT

Randy L. Hoffman, et al.

FILING DATE

Herewith

GROUP

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	4A				
	4B				
	4C				
	4D				
	4E				
	4F				
	4G				
	4H				
	4I				
	4J				
	4K				

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	4L				
	4M				
	4N				
	4O				
	4P				

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

MF	4Q	Ohya, Yutaka, et al., "Thin Film Transistor of ZnO Fabricated by Chemical Solution Deposition", Jpn. J. Appl. Phys., Vol. 40, Part 1, No. 1, pp. 297-298 (January, 2001).
MF	4R	Pallecchi, Ilaria, et al. "SrTiO3-based metal-insulator-semiconductor heterostructures" Applied Physics Letters, Vol. 78, No. 15, pp. 2244-2246 (April 9, 2001).
MF	4S	Prins, M. W. J., et al., "A ferroelectric transparent thin-film transistor", Appl. Phys. Lett., Vol. 68, No. 25, pp. 3650-3652 (June 17, 1996).

EXAMINER

DATE CONSIDERED

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

200315719-1

APPLICATION NO.

CONFIRMATION NO.

APPLICANT

Randy L. Hoffman, et al.

FILING DATE

Herewith

GROUP

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	5A				
	5B				
	5C				
	5D				
	5E				
	5F				
	5G				
	5H				
	5I				
	5J				
	5K				

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	5L					
	5M					
	5N					
	5O					
	5P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

NSP	5Q	Seager, C.H., et al., "Charge Trapping and device behavior in ferroelectric memories", Appl. Phys. Lett., Vol. 68, No. 19, pp. 2660-2662 (May 6, 1996).
NSP	5R	Uneno, K., et al. "Field-effect transistor on SrTiO ₃ with sputtered Al ₂ O ₃ gate insulator", Applied Physics Letters, Vol. 83, No. 9, pp. 1755-1757 (September 1, 2003).
NSP	5S	Wöllenstein, Jürgen, et al., "An insulated gate thin-film transistor using SnO ₂ as semiconducting channel, a possible new gas sensor device" The 11th European Conference on Solid State Transducers, pp. 471-474 (September 21-24, 1997).

EXAMINER

DATE CONSIDERED

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

200315719-1

APPLICATION NO.

CONFIRMATION NO.

APPLICANT

Randy L. Hoffman, et al.

FILING DATE

Herewith

GROUP

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	6A			
	6B			
	6C			
	6D			
	6E			
	6F			
	6G			
	6H			
	6I			
	6J			
	6K			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	6L				
	6M				
	6N				
	6O				
	6P				

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

6Q	Yoshida, A., "Three Terminal Field Effect Superconducting Device Using SrTiO ₃ Channel" IEEE Transactions on Applied Superconductivity, Vol. 5, No. 2, pp. 2892-2895 (June, 1995).
6R	Solid-State Electronics, Vol. 7, Pergamon Press, Notes pp. 701-702 (1964).
6S	Anonymous, "Transparent and/or memory thin film transistors in LCD's and PLEAD_" Research Disclosure, p. 890 (July 1998).

EXAMINER

DATE CONSIDERED

3/19/2007